

128K x 8 Static RAM Module

Features

- High-density 1-megabit SRAM module
- High-speed CMOS SRAMs
 Access time of 35 ns
- Low active power
 - 1.1W (max.)
- SMD technology
- TTL-compatible inputs and outputs
- Low profile
 - Max. height of 0.65 in.
- Small PCB footprint

Functional Description

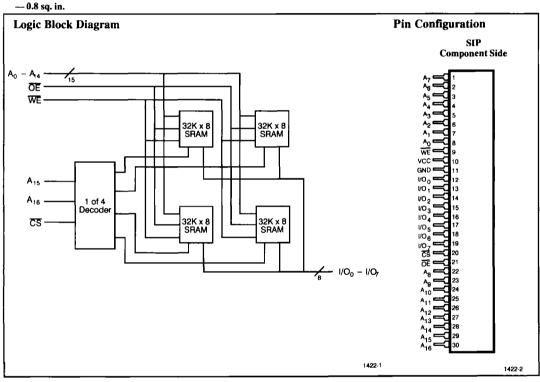
The CYM1422 is a high-performance I-megabit static RAM module organized as 128K words by 8 bits. The module is constructed using four 32K x 8 static RAMs in SOICs mounted onto a single-sided multi-layer epoxy laminate board with pins. A decoder is used to interpret the higher-order addresses (A_{15} and A_{16}) and to select one of the four RAMs.

Writing to the memory module is accomplished when the chip select (\overline{CS}) and write enable (\overline{WE}) inputs are both LOW. Data on the eight input/output pins $(1/O_0$ through

 I/O_7) is written into the memory location specified on the address pins (A_0 through A_{36}).

Reading the device is accomplished by taking chip select (CS) and output enable (OE) LOW while WE remains inactive or HIGH. Under these conditions, the contents of the memory location specified on the address pins will appear on the eight data input/output pins.

The input/output pins remain in a highimpedance state unless the module is selected, outputs are enabled, and write enable (WE) is HIGH.



Selection Guide

	1422-35	1422-45	1422-55
Maximum Access Time (ns)	35	45	55
Maximum Operating Current (mA)	200	200	200
Maximum Standby Current (mA)	140	140	140



Maximum Ratings

(Above which the useful life may be impaired.)

DC Input Voltage 0.5V to +	7.0V
Output Current into Outputs (LOW) 2	0 mA

Operating Range

Range	Ambient Temperature	V _{CC}	
Commercial	0°C to + 70°C	5V ± 10%	

Electrical Characteristics Over the Operating Range

			1422		
Parameters	Description	Test Conditions	Min.	Max.	Units
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0 \text{ mA}$	2.4		V
V _{OL}	Output LOW Voltage	$V_{\rm CC}$ = Min., $I_{\rm OL}$ = 8.0 mA		0.4	V
V_{IH}	Input HIGH Voltage		2.2	v_{cc}	V
$\overline{v_{lL}}$	Input LOW Voltage		-0.5	0.8	V
I _{IX}	Input Load Current	$GND \leq V_{I} \leq V_{CC}$	-15	+15	μА
I _{OZ}	Output Leakage Current	$GND \le V_O \le V_{CC}$, Output Disabled	-15	+15	μΑ
I_{CC}	V _{CC} Operating Supply Current	$V_{CC} = Max., I_{OUT} = 0 \text{ mA},$ $CS \le V_{IL}$		200	mA
I _{SB1}	Automatic CS Power-Down Current[1]	Max. V_{CC} ; $\overline{CS} \ge V_{IH}$ Min. Duty Cycle = 100%		140	mA
I _{SB2}	Automatic CS Power-Down Current[1]	Max. V_{CC} ; $\overline{CS} \ge V_{CC} - 0.3V$, $V_{IN} \ge V_{CC} - 0.3V$ or $V_{IN} \le 0.3V$		80	m A

Capacitance[2]

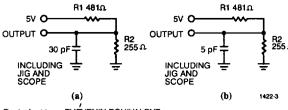
Parameters	Description	Test Conditions	Max.	Units
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	40	рF
C _{OUT}	Output Capacitance	$V_{CC} = 5.0V$	35	pF

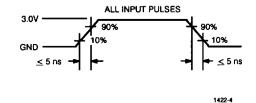
Notes

A pull-up resistor to V_{CC} on the CS input is required to keep the device deselected during V_{CC} power-up, otherwise I_{SB} will exceed values given.

2. Tested on a sample basis.

AC Test Loads and Waveforms





Equivalent to: THEVENIN EQUIVALENT



Switching Characteristics Over the Operating Range[3]

		1422	1422-35		1422-45		1422-55	
Parameters	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
READ CYCLI	E				•	•		
t _{RC}	Read Cycle Time	35		45		55		ns
t _{AA}	Address to Data Valid		35		45		55	ns
t _{OHA}	Data Hold from Address Change	3		3		3		ns
t _{ACS}	CS LOW to Data Valid		35	1	45		55	ns
t _{DOE}	OE LOW to Data Valid		20	İ	25		30	ns
tLZOE	OE LOW to Low Z	3		3		3		ns
tHZOE	OE HIGH to High Z		20		20		20	ns
tLZCS	CS LOW to Low Z ^[4]	3		3		3		ns
tHZCS	CS HIGH to High Z ^[4, 5]		20		20		20	ns
tpU	CS LOW to Power-Up	0	<u> </u>	0		0		ns
t _{PD}	CS HIGH to Power-Down		35		45		55	ns
WRITE CYCI	E[6]	•				•		
twc	Write Cycle Time	35	·	45		55		ns
t _{SCS}	CS LOW to Write End	30		40		45		ns
t _{AW}	Address Set-Up to Write End	30		40		45		ns
t _{HA}	Address Hold from Write End	5		5		5		ns
t _{SA}	Address Set-Up to Write Start	5		5		5		ns
t _{PWE}	WE Pulse Width	25		35		35		ns
t _{SD}	Data Set-Up to Write End	20		20		20		ns
t _{HD}	Data Hold from Write End	3		5		5		ns
tLZWE	WE HIGH to Low Z ^[4]	3		3		3		ns
tHZWE	WE LOW to High Z[4,5]	0	20	0	25	0	25	ns

Notes:

- Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V, input levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance. At any given temperature and voltage condition, t_{HZCS} is less than t_{LZCS} for any given device. These parameters are guaranteed and not 100% tested.

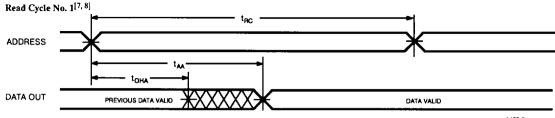
- The internal write time of the memory is defined by the overlap of \overline{CS} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write,

and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

- WE is HIGH for read cycle.

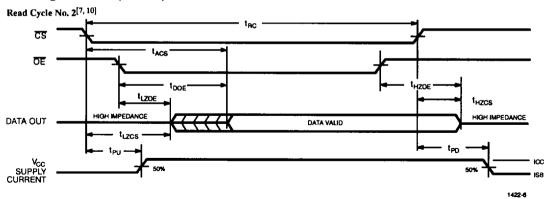
- Device is continuously selected, S = V_{IL} and OE = V_{IL}.
 Data I/O will be high impedance if OE = V_{IH}.
 Address valid prior to or coincident with CS transition LOW.
- 11. If CS goes HIGH siumultaneously with WE HIGH, the output remains in a high-impedance state.

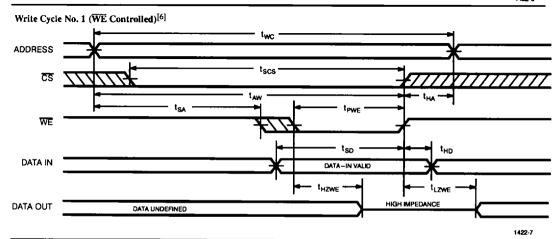
Switching Waveforms[9]

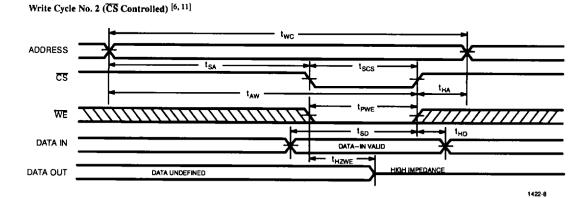




Switching Waveforms (continued)









Truth Table

CS	ŌE	WE	Inputs/Outputs	Mode
Н	Х	Х	High Z	Deselect/Power-Down
L	L	Н	Data Out	Read
L	Х	L	Data In	Write
L	Н	Н	High Z	Deselect

Document #: 38-M-00003-B

Ordering Information

Speed (ns)	Ordering Code	Package Type	Operating Range
35	CYM1422PS-35C	PS03	Commercial
45	CYM1422PS-45C	PS03	Commercial
55	CYM1422PS-55C	PS03	Commercial